

## Automotive Discrete Group (ADG) Power Transistor Macro-Division

#### **Process Change Notification**

#### STAC2942BW; STAC3932B; STAC4932B, STAC4932F, STAC4932F1MR New RJR 5FT80092 frame qualification

Dear Customer,

Following the continuous improvement of our service and in order to increase productivity, we would like to inform you of a qualification of a new RJR frame 5FT80092 to replace the actual RJR frame 5FT86666.

In the next pages, we are reporting all the details of the change and the plan to release it in production

The change has been classified as **Class 1** according to the ST internal rules.

	Assessment of impact on Supply Chain regarding following aspects - contractual agreements - technical interface of processability / manufacturability of customer - form, fit, function, quality performance, reliability		ining s on ply in?
ID	Type of change	No	Yes
SEM-PA-02	Change of leadframe base material	Х	

The qualification of the change was completed.

Sincerely Yours!

	Tech name
ST Part number:	ST PN: STAC2942BW; STAC3932B; STAC4932B, STAC4932F, STAC4932F1MR Package: STAC780
Reason and background of the change	Replacement of the actual RJR Frame 5FT86666 with the new one 5FT80092 to secure supply chain.
Detailed description of change(s), including affected type of changes	Width lead dimension reduction and plating material composition
Impact on form, fit, function, or reliability.	New lead frame will be compatible with the old one. See attached presentation
Datasheet	YES
Benefit of the change	Secure production continuity
Qualification Plan and Implementation date for change	The qualification has been completed according to the attached qualification plan
Traceability Information	Dedicated Finish Good
PPAP Update	NA



#### **RELIABILITY EVALUATION REPORT**

New STAC780-4F/B packages for DMOS products qualification (silicon test vehicle 4925) Process Change

**General Information** 

Commercial Product : STAC3932F - STAC3932B

Product Line :4925

Product Description : RF DMOS

Package :STAC780-4F / STAC780-4B

Silicon Technology : DMOS

**Division** : Power Transistor Division

Traceability							
Diffusion Plant Assembly Plant	:CT6 : BOUSKOURA 2 - MOROCCO						
Reliab	ility Assessment						
Passed							

**Disclaimer:** this report is a summary of the qualification plan results performed in good faith by STMicroelectronics to evaluate the electronic devices conformance to its specific mission profile for Automotive Application. This report and its contents shall not be disclosed to a third party, except in full, without previous written agreement by STMicroelectronics or under the approval of the author (see below)

#### **REVISION HISTORY**

Version	Date	Author	Changes description
1.0	05-March-2020	Michele PANZARELLA	

#### **APPROVED BY:**

CORRADO CAPPELLO
ADG Q&R DEPARTMENT - CATANIA
ST MICROELECTRONICS

Choose an item, RER Id. N. 909B/20



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#### 1. RELIABILITY EVALUATION OVERVIEW

#### 1.10bjective

To evaluate the new STAC780-4F/B packages for DMOS products.

#### 1.2 Reliability Test Plan

Reliability tests performed on this device are in agreement with internal spec 0061692 and are listed in the Test Plan For details on test conditions, generic data used and spec reference see test results summary at Par.3

#### 1.2.1 TEST PLAN

#### **TABLE 2**

#	Stress	Abrv	Reference	Test Flag	Comments
1	Pre and Post-Stress Electrical Test	TEST	User specification or supplier's standard Specification	Y	
2	High Temperature Storage Life	HTSL	JESD22B-101	Υ	
3	Temperature Cycling	TC	JESD22A-104	Υ	
4	Mechanical Sequence	MS	JESD22-B103B	Υ	

Choose an item. RER Id. N. 909B/20



#### 1.3 CONCLUSION

On the basis of the positive reliability assessment, the new STAC780-4F/B package for DMOS products can be considered qualifiable from reliability point of view.

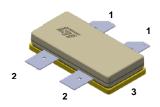
#### 2. DEVICE/TEST VEHICLE CHARACTERISTICS

#### 2.1 Generalities

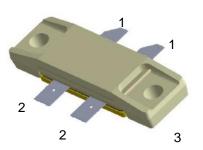
The STAC3932B and the STAC3932F are N-channel MOS field-effect RF power transistor. It is intended for use in 100 V DC large signal applications up to 250 MHz.

#### 2.2 Pin connection

STAC780-4F (flangeless)



1.Drain 2.Gate 3.Source STAC780-4B (bolt-down)



1.Drain2.Gate3.Source



#### 2.5 Traceability

Wafer fab information	
Wafer fab manufacturing location	CT6
Wafer diameter (inches)	6"
Silicon process technology	DMOS
Die finishing front side (passivation)	SiN (nitride)
Die finishing back side	Au/As
Die area (Stepping die size)	6980 um x 1430 um
Metal levels/Materials	1 / AlCu

Assembly Information	
Assembly plant location	BOUSKOURA - MOROCCO
Package description	STAC780-4B/F
Frame	FRAME SW0800 4L 380x780 LCP STAC780-4PPF BASE THERMAL BeO 385x810 STAC244-KAI
Die attach material	AuSi eutectic
Wires bonding materials/diameters	WIRE Al-Si D1.5
Molding compound	LID LCP

Reliability Testing Information				
Reliability laboratory location	Catania			
Electrical testing location (*)	Catania			
Tester (*)	Tesec			



#### 3. TESTS RESULTS SUMMARY

#### 3.1 Lot Information

Lot #	Line	PN	Packages	Note	
2	4925	STAC3932F1	STAC780-4F	(flangeless)	
3		STAC3932B	STAC780-4B	(bolt-down)	

#### 3.2 Test results summary

						Failure/SS		
Test	PC	Std ref.	Conditions	SS	Steps	Lot 1	Lot 2	Lot3
TEST		User specification	All qualification parts tested per the requirement appropriate device specification.	nts of the		80	80	80
External visual		JESD22 B-101	All devices submitted for testing			80	80	80
Parametric Verification		User specification	All parameters according to user specification at room temperature and the maximum 135 specified operating temperature			80	80	80
Die Oriented	Tes	ts						
					168 H	0/45	0/45	0/45
HTSL	N	JESD22 A-103	Tj = 175°C	135	500 H	0/45	0/45	0/45
					1000 H	0/45	0/45	0/45
Package Orio	ente	d Tests						
		150500			100cy	0/25	0/25	0/25
TC	Ν	JESD22 A-104	TA=-65°C TO 150°C	75	200cy	0/25	0/25	0/25
					500cy	0/25	0/25	0/25
MS	N	JESD22- B103B	VIBRATION a=20g; f=100/2000 Hz; 4' x 3 orient. x 4 cycles	30	After stress	0/10	0/10	0/10

Choose an item. RER Id. N. 909B/20

# **STAC780-4 vs STAC244**

5FT80092 vs 5FT8666 lead frame

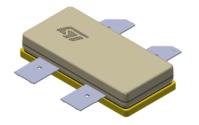
Gan & Power RF Marketing team February 25th, 2020





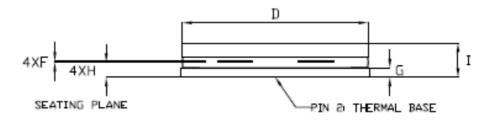
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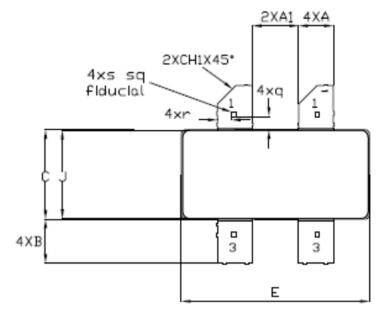




## STAC780-4F

DIMENSIONS								
REF.	DAT	TA BOOK (mm)		DATA	A BOOK (inches)			
DIM	NOM	MIN	MAX	NOM	MIN	MAX		
A	-	3.76	3.86	-	0.148	0.152		
Al		5.03	5.13		0.198	0.202		
В	-	4.57	5.08	-	0.180	0.200		
С	-	9.65	9.91	-	0.380	0.390		
D	-	20.17	20.37	-	0.794	0.802		
E	-	20.45	20.70	-	0.805	0.815		
F	-	0.11	0.17	-	0.005	0.007		
G	-	0.97	1.14	-	0.038	0.045		
H	-	1.52	1.70	-	0.060	0.067		
I	-	3.18	4.32	-	0.125	0.170		
J	-	9.52	9.78	-	0.375	0.385		
q	1.37	-	-	0.057	-	-		
r	1.52	-	-	0.060	-	-		
s	0.51	-	-	0.020	-	-		
CHl	2.03	-	-	0.08	-	-		







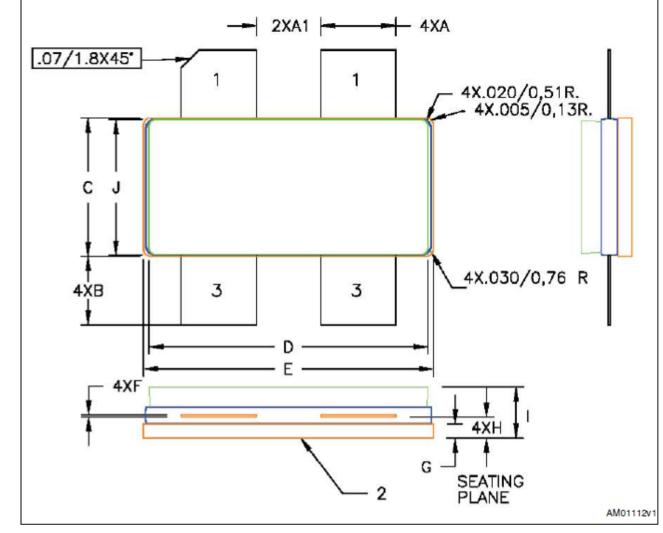




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## STAC244F

Dim	mm.		Inch		
Dlm.	Min	Max	MIn	Max	
Α	5.10	5.59	200	220	
A1	4.32	4.83	170	190	
В	4.32	5.33	170	210	
С	9.65	9.91	380	390	
D	19.61	20.02	772	788	
E	20.45	20.70	805	815	
F	0.08	1.15	0.003	0.006	
G	0.89	1.14	0.035	0.045	
Н	1.45	1.70	0.057	0.067	
1	3.18	4.32	0.125	0.170	
J	9.27	9.53	0.365	0.375	







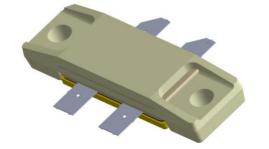


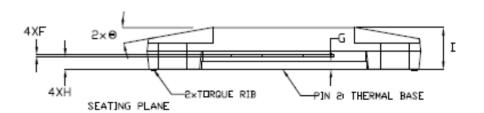
		DIM	ENSI	ONS		
REF.	DAT	A BOOK (	mm)	DATA	A BOOK (ii	nches)
$\mathbf{DIM}$	NOM	MIN	MAX	NOM	MIN	MAX
A	-	3.76	3.86	-	0.148	0.152
Al	-	5.03	5.13	-	0.198	0.2020
В	-	4.57	5.08	-	0.180	0.200
С	-	9.65	9.91	-	0.380	0.390
D	-	17.78	18.08	-	0.700	0.712
E	-	33.88	34.19	-	1.334	1.346
F	-	0.11	0.17	-	0.005	0.007
G	-	0.97	1.14	-	0.038	0.045
H	-	1.52	1.70	-	0.060	0.067
I	-	4.83	5.33	-	0.190	0.210
J	-	9.52	9.78	-	0.375	0.385
K	-	27.69	28.19	-	1.090	1.110
L	3.25	3.20	3.30	0.128	0.126	0.130
M	3.51	3.43	3.58	0.138	0.135	0.141
N	3.38	3.30	3.45	0.133	0.130	0.136
P	7.21	7.14	7.29	0.284	0.281	0.287
q	1.37	-	-	0.057	-	-
r	1.52	-	-	0.060	-	-
S	0.51	-	-	0.020	-	-
Θ	10°	-	-	10°	-	-
CHl	2.03	-	-	0.08	-	-
CH2	1.52	_	-	0.060	-	-

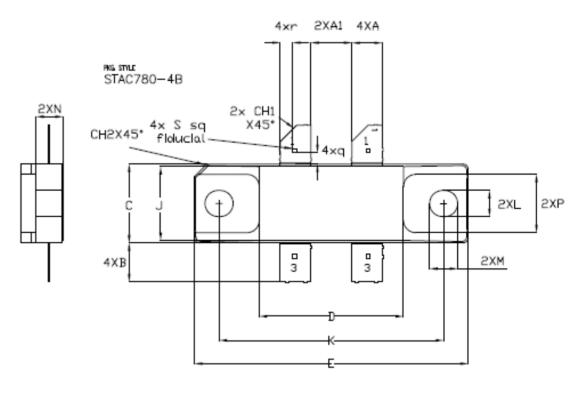




## STAC780-4B







PD4	CORRECTION N
1	DRAIN
8	SOURCE
3	GATE



Dim.	mm				
Dilli.	Min.	Тур.	Max.		
Α	5.08		5.59		
A1	4.32		4.83		
В	4.32		5.33		
С	9.65		9.91		
D	17.78		18.08		
E	33.88		34.19		
F	0.10		0.15		
G		1.02			
Н	1.45		1.70		
1	4.83		5.33		
J	9.27		9.52		
К	27.69		28.19		
L	3.12	3.23	3.33		

3.45

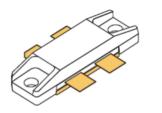
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## STAC244B

STAC244B Air cavity

